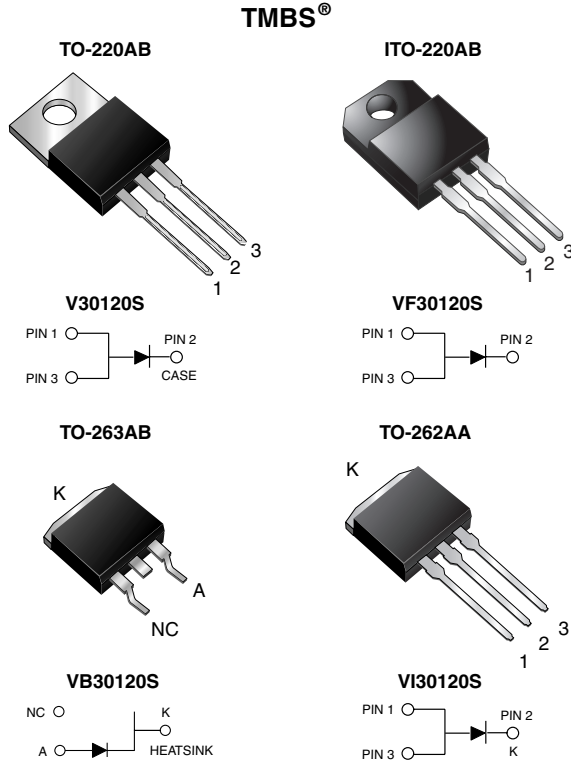


## High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.43\text{ V}$  at  $I_F = 5\text{ A}$



### FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

### MECHANICAL DATA

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS compliant, commercial grade

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

$I_{F(AV)}$	30 A
$V_{RRM}$	120 V
$I_{FSM}$	300 A
$V_F$ at $I_F = 30\text{ A}$	0.74 V
$T_J$ max.	150 °C

### MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V30120S	VF30120S	VB30120S	VI30120S	UNIT
Maximum repetitive peak reverse voltage	$V_{RRM}$		120			V
Maximum average forward rectified current (fig. 1)	$I_{F(AV)}$		30			A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	$I_{FSM}$		300			A
Non-repetitive avalanche energy at $T_J = 25\text{ °C}$ , $L = 100\text{ mH}$	$E_{AS}$		180			mJ
Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$ , 1 kHz, $T_J = 38\text{ °C} \pm 2\text{ °C}$	$I_{RRM}$		0.5			A
Voltage rate of change (rated $V_R$ )	dV/dt		10 000			V/ $\mu\text{s}$
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$	$V_{AC}$		1500			V
Operating junction and storage temperature range	$T_J, T_{STG}$		- 40 to + 150			°C

ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>A</sub> = 25 °C	V <sub>BR</sub>	120 (minimum)	-	V
Instantaneous forward voltage <sup>(1)</sup>	I <sub>F</sub> = 5 A I <sub>F</sub> = 15 A I <sub>F</sub> = 30 A	T <sub>A</sub> = 25 °C	V <sub>F</sub>	0.50 0.70 0.99	- - 1.10	V
	I <sub>F</sub> = 5 A I <sub>F</sub> = 15 A I <sub>F</sub> = 30 A	T <sub>A</sub> = 125 °C		0.43 0.60 0.74	- - 0.82	
Reverse current <sup>(2)</sup>	V <sub>R</sub> = 90 V	T <sub>A</sub> = 25 °C T <sub>A</sub> = 125 °C	I <sub>R</sub>	18 12	- -	μA mA
	V <sub>R</sub> = 120 V	T <sub>A</sub> = 25 °C T <sub>A</sub> = 125 °C		- 22	500 35	μA mA

Notes

<sup>(1)</sup> Pulse test: 300 μs pulse width, 1 % duty cycle

<sup>(2)</sup> Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V30120S	VF30120S	VB30120S	VI30120S	UNIT
Typical thermal resistance per diode	R <sub>θJC</sub>	1.6	4	1.6	1.6	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V30120S-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	VF30120S-E3/4W	1.76	4W	50/tube	Tube
TO-263AB	VB30120S-E3/4W	1.39	4W	50/tube	Tube
TO-263AB	VB30120S-E3/8W	1.39	8W	800/reel	Tape and reel
TO-262AA	VI30120S-E3/4W	1.46	4W	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES

(T<sub>A</sub> = 25 °C unless otherwise noted)

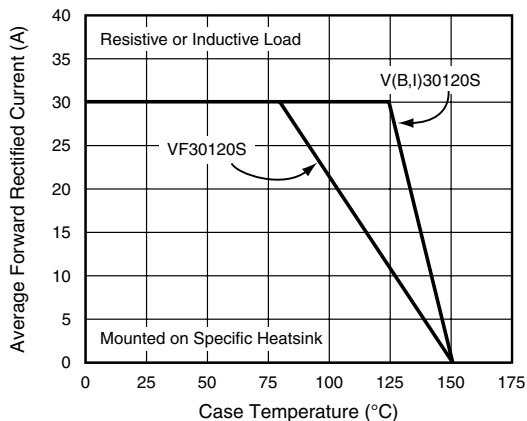


Figure 1. Forward Current Derating Curve

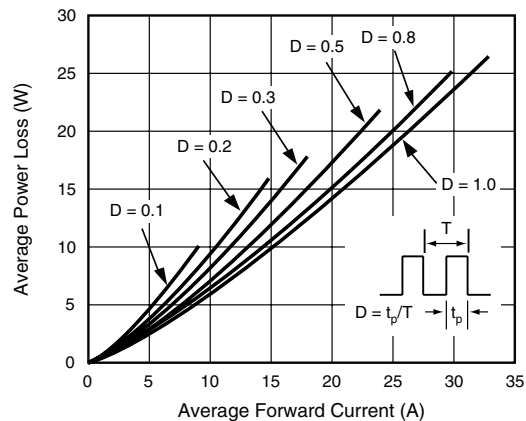


Figure 2. Forward Power Loss Characteristics Per Diode

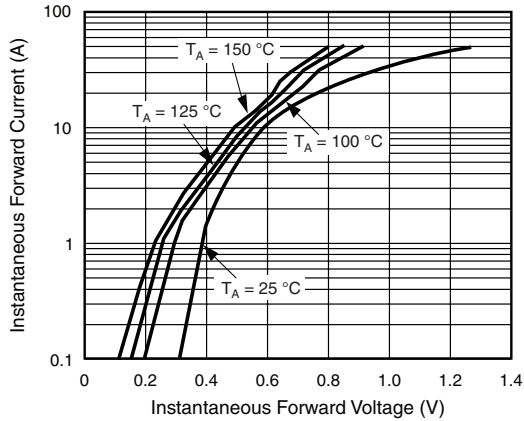


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

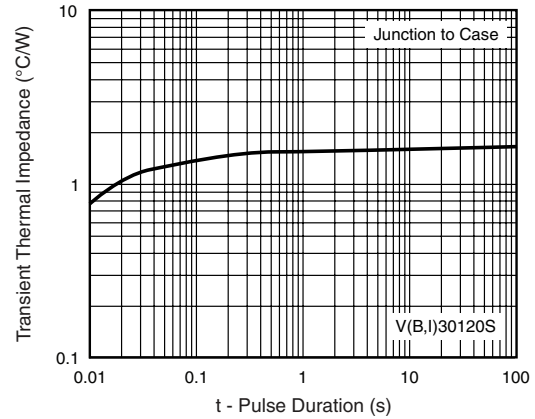


Figure 6. Typical Transient Thermal Impedance Per Diode

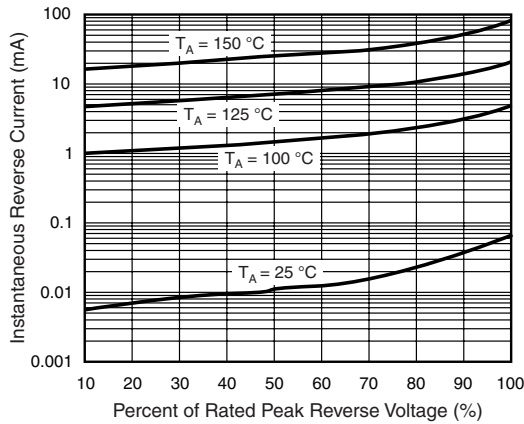


Figure 4. Typical Reverse Characteristics Per Diode

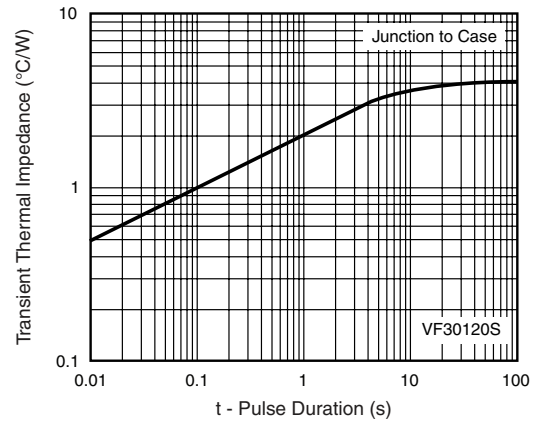


Figure 7. Typical Transient Thermal Impedance Per Diode

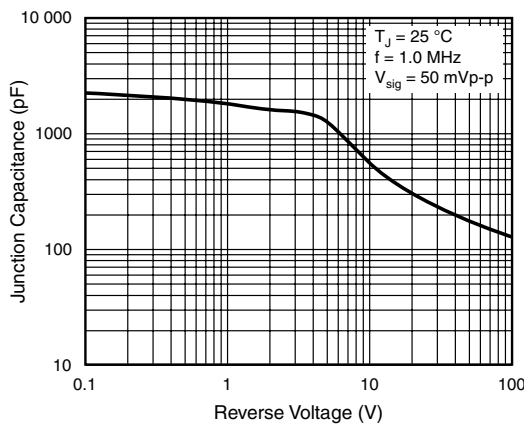


Figure 5. Typical Junction Capacitance Per Diode

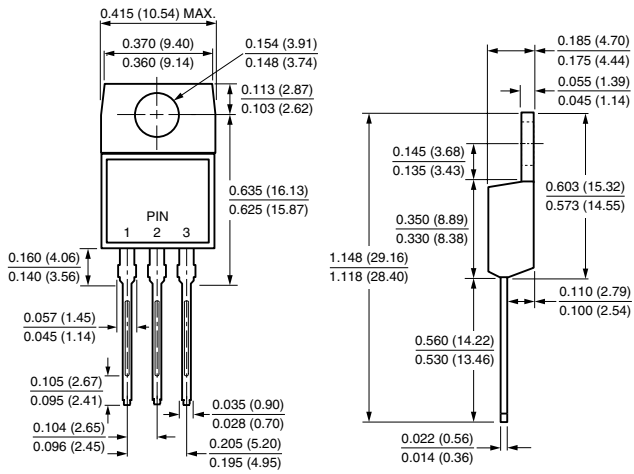
# V30120S, VF30120S, VB30120S & VI30120S

Vishay General Semiconductor

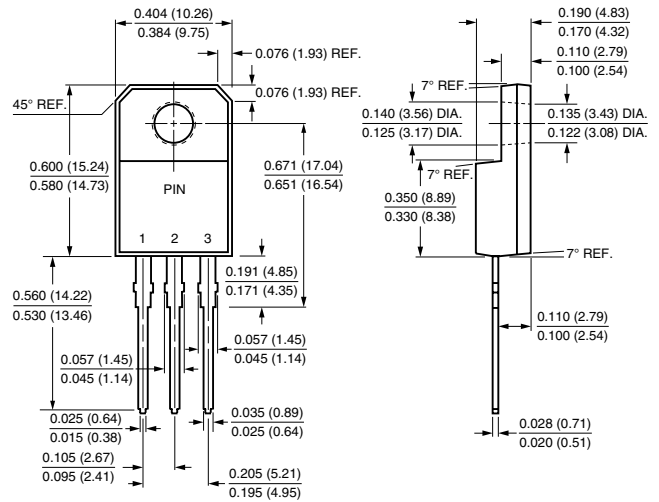


## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

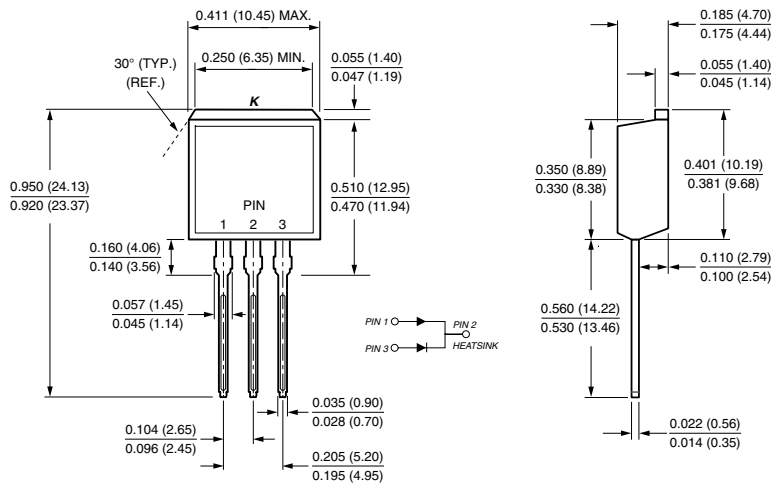
TO-220AB



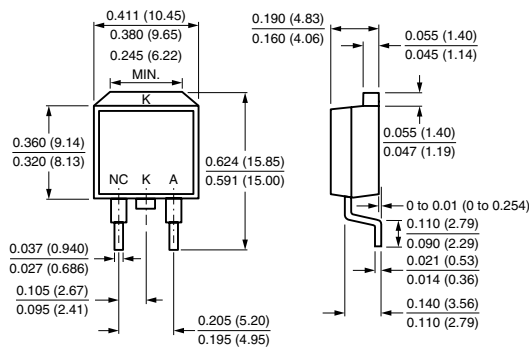
ITO-220AB



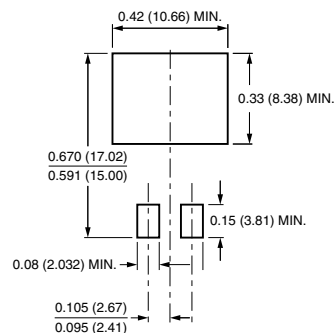
TO-262AA



TO-263AB



Mounting Pad Layout





## Disclaimer

All product specifications and data are subject to change without notice.

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